2SB1182

PNP SILICON TRANSISTOR

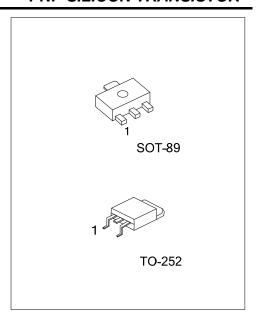
MEDIUM POWER LOW VOLTAGE TRANSISTOR

DESCRIPTION

The UTC 2SB1182 is a medium power low voltage transistor, designed for audio power amplifier, DC-DC converter and voltage regulator.

FEATURES

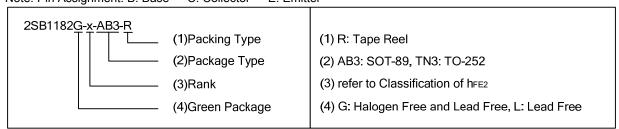
- * High current output up to 3A
- * Low saturation voltage



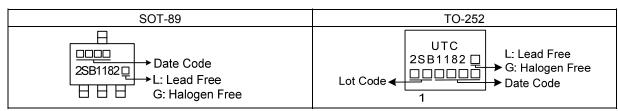
ORDERING INFORMATION

Ordering Number		Doolsogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SB1182L-x-AB3-R	2SB1182G-x-AB3-R	SOT-89	В	С	E	Tape Reel	
2SB1182L-x-TN3-R	2SB1182G-x-TN3-R	TO-252	В	С	Е	Tape Reel	

Note: Pin Assignment: B: Base C: Collector E: Emitter



MARKING



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■ **ABSOLUTE MAXIMUM RATINGS** (T_A = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	-40	V
Collector-Emitter Voltage		V _{CEO}	-32	V
Emitter-Base Voltage	_	V _{EBO}	-5	V
Collector Current	DC	Ic	-2	Α
	Pulse	I _{CP}	-3	Α
Base Current		I _B	-0.6	Α
Collector Dissipation (T _C =25°C)	SOT-89	- Pc	3.5	W
Collector Dissipation (1c=25 C)	TO-252		10	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_CBO	I _C =-50μA	-40			V
Collector-Emitter Breakdown Voltage	BV_CEO	I _C =-1mA	-32			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =-50μA	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-20V			-1	μΑ
Collector Cut-Off Current	I _{CEO}	V _{CE} =-20V			-1	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-4V			-1	μΑ
DC Current Gain(Note 1)	h_{FE}	V_{CE} =-3V, I_{C} =-0.5A	120		390	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I _C =-2A, I _B =-0.2A		-0.5	-0.8	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =-2A, I _B =-0.2A		-1.0	-2.0	V
Current Gain Bandwidth Product	f_{T}	V _{CE} =-5V, I _E =0.5 A, ,f=100MHz		100		MHz
Output Capacitance	C _{OB}	V _{CB} =-10V, I _E =0 A,f=1MHz		50		pF

Note 1: Pulse test: P_W < 300µs, Duty Cycle < 2%

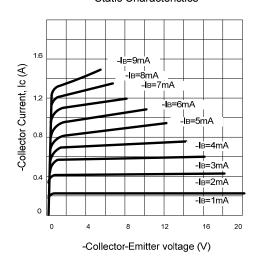
■ CLASSIFICATION OF h_{FE2}

RANK	Q	R		
RANGE	120 ~ 270	180 ~ 390		

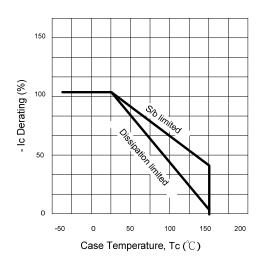


■ TYPICAL CHARACTERICS

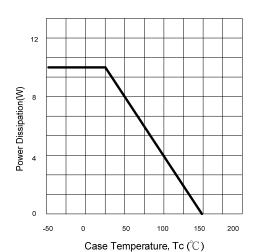




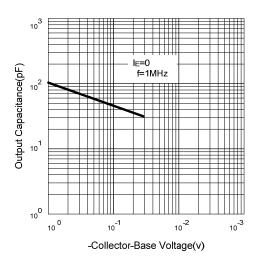
Derating Curve of Safe Operating Areas



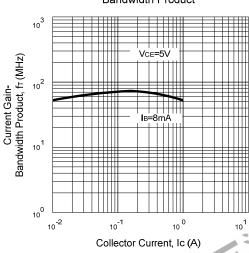
Power Derating



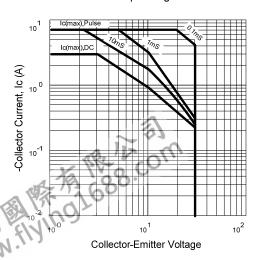
Collector Output Capacitance



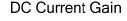
Current Gain-Bandwidth Product

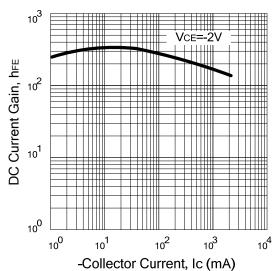


Safe Operating Area

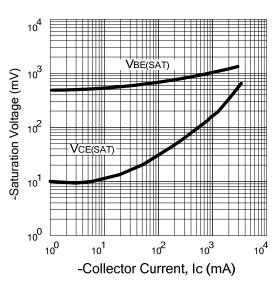


■ TYPICAL CHARACTERICS (Cont.)





Saturation Voltage



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